Silicon NPN Power Transistors BU932

DESCRIPTION
·With TO-3 package
·DARLINGTON

APPLICATIONS
·Automotive ignition applications
·Inverters circuits for motor controls

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

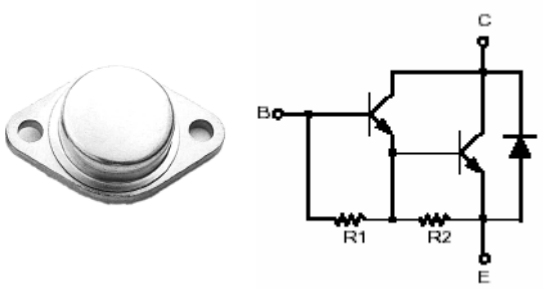

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	450	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		15	A
I_{CM}	Collector current-peak		30	A
I_B	Base current		1	A
I_{BM}	Base current-peak		5	A
P_T	Total power dissipation	T_C≤25□	150	W
T_j	Junction temperature		200	□
T_{stg}	Storage temperature		-40~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}c}$	Thermal resistance from junction to case	1.0	□/W

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA ; I_B=0	450			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=8A; I_B=150mA			1.8	V
V_{BEsat}	Base-emitter saturation voltage	I_C=8A; I_B=150mA			2.2	V
I_{CEO}	Collector cut-off current	V_{CE}=450V ;I_B=0			1.0	mA
I_{CES}	Collector cut-off current	V_{CE}=450V ;V_{BE}=0 T_C=125□			1.0 5.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			50	mA
h_{FE}	DC current gain	I_C=5A ; V_{CE}=10V	300			
V_F	Diode forward voltage	I_F=10A			2.8	V

PACKAGE OUTLINE

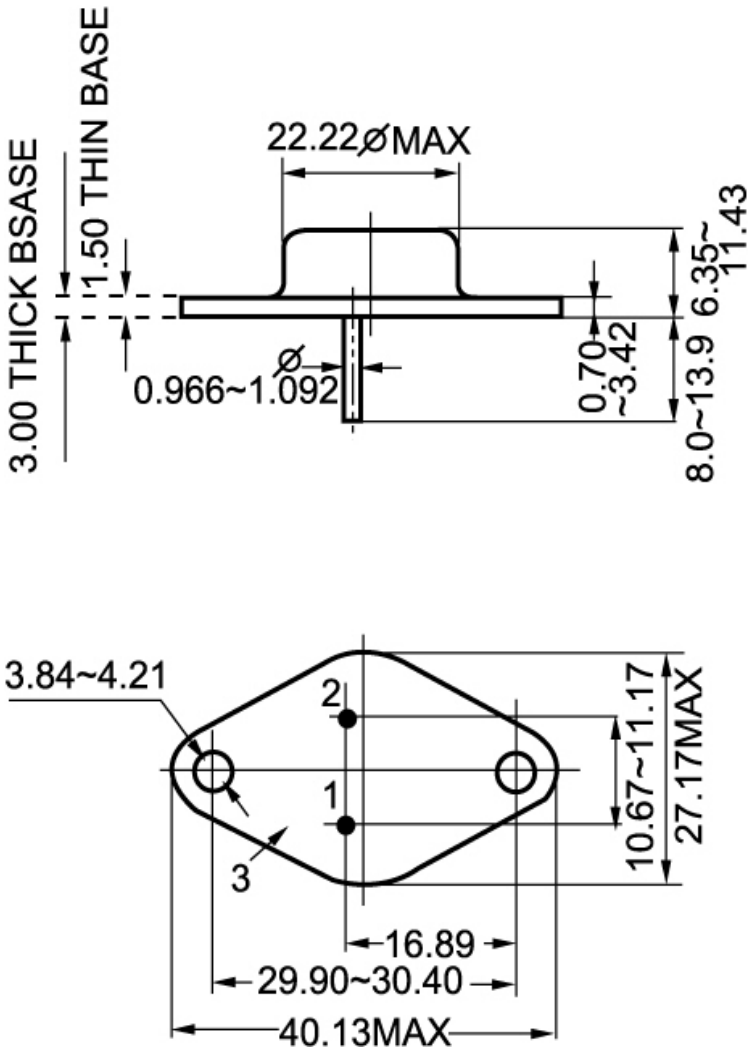

Fig.2 Outline dimensions